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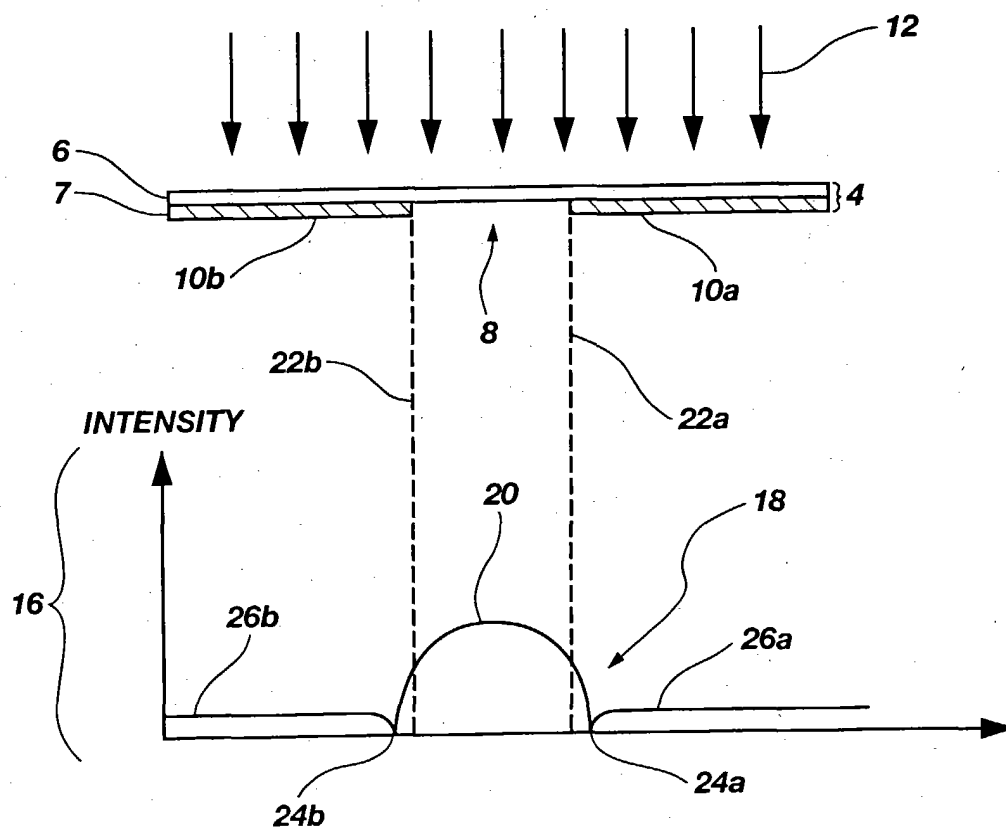


Fig. 1
(PRIOR ART)

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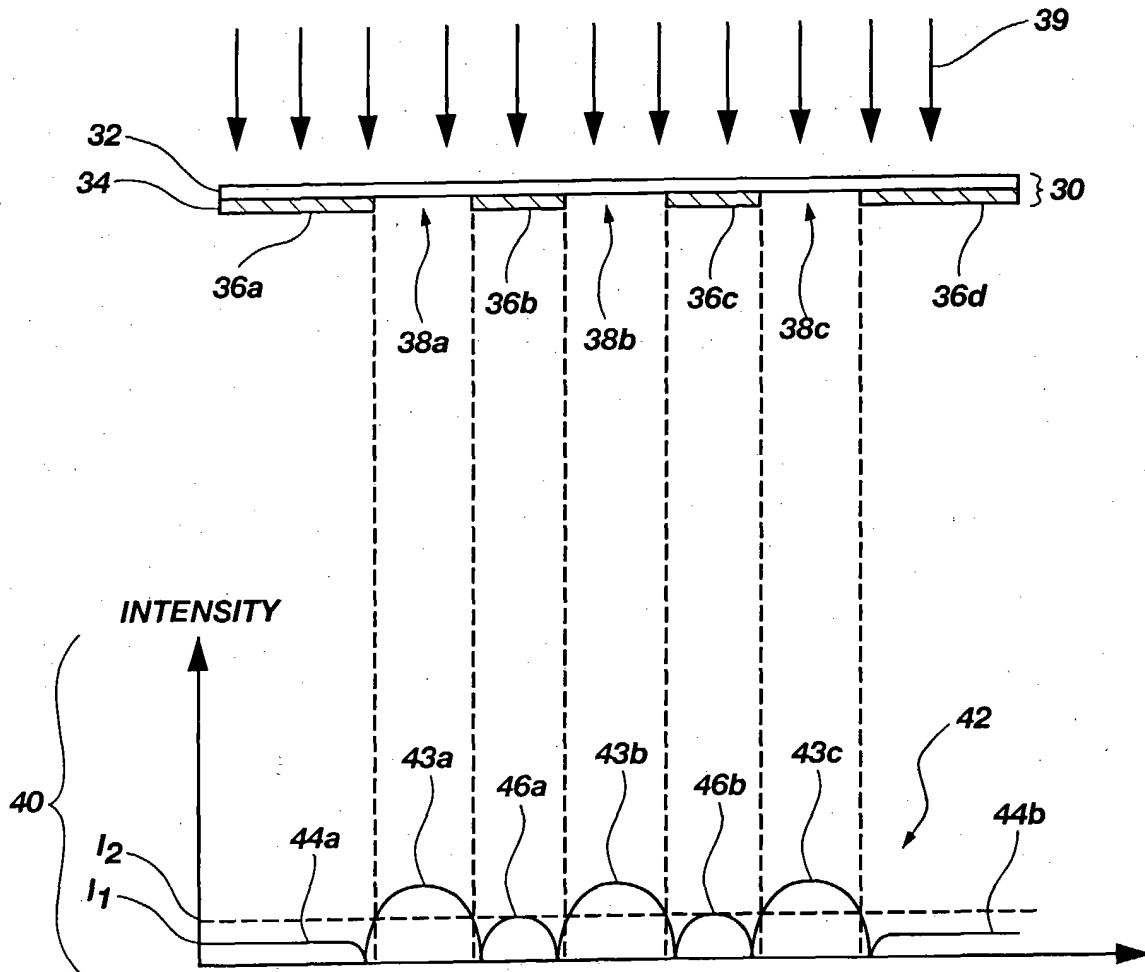


Fig. 2
(PRIOR ART)

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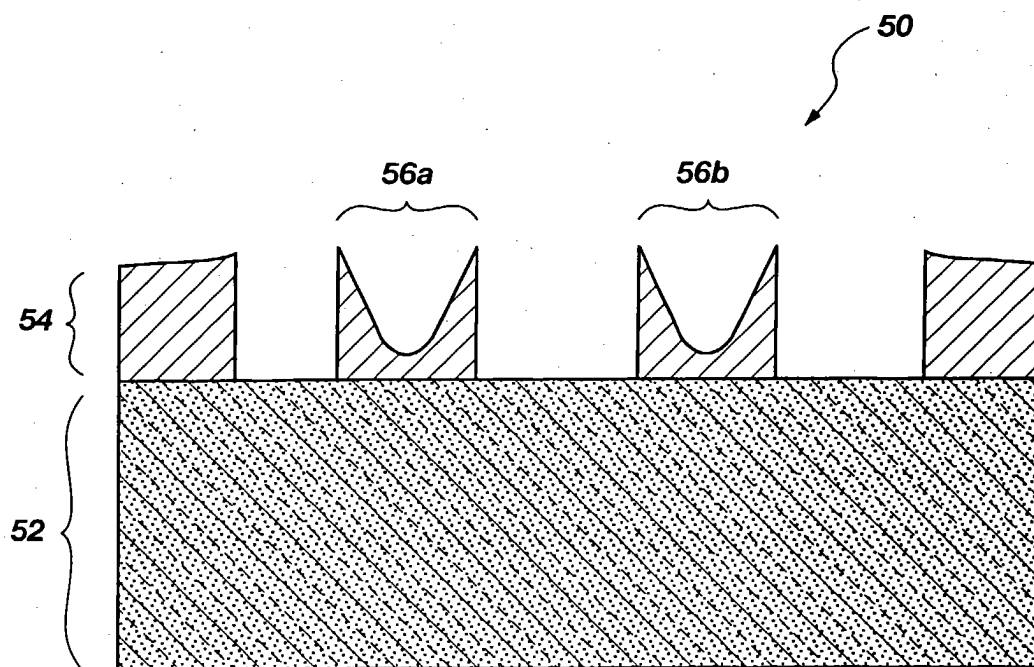


Fig. 3
(PRIOR ART)

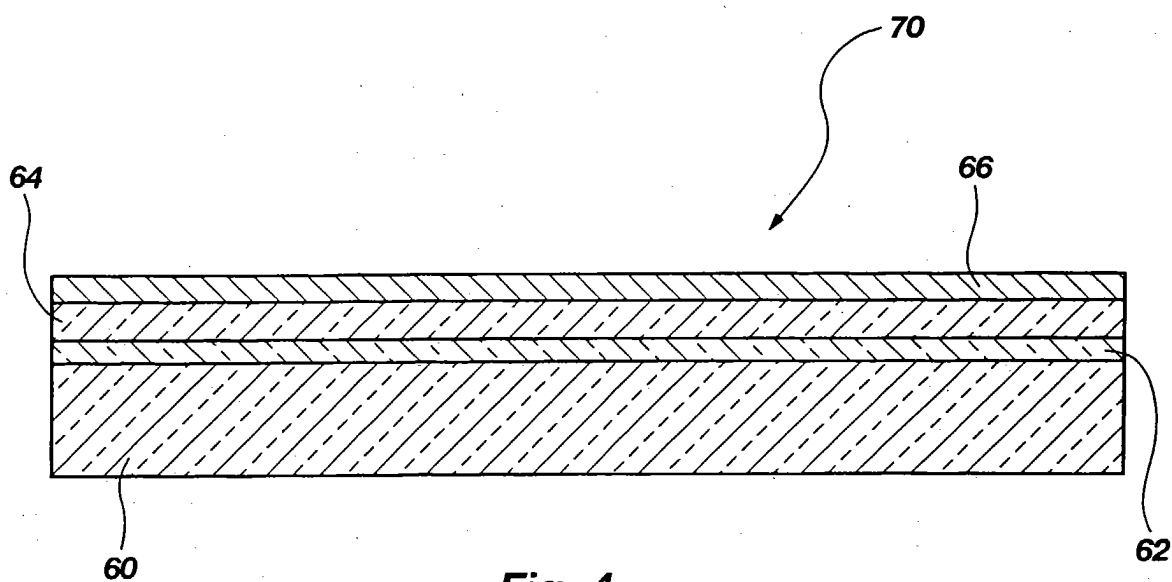


Fig. 4

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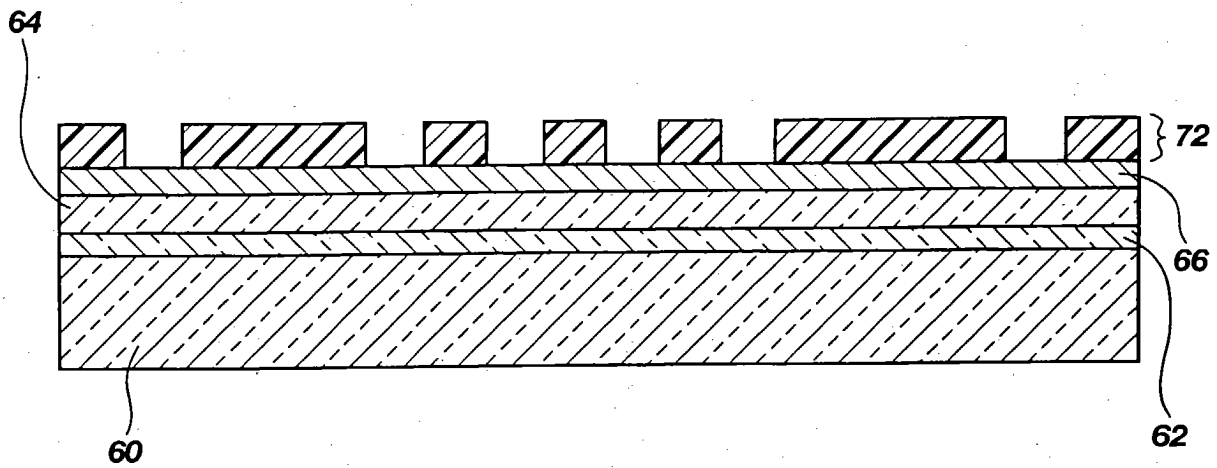


Fig. 5

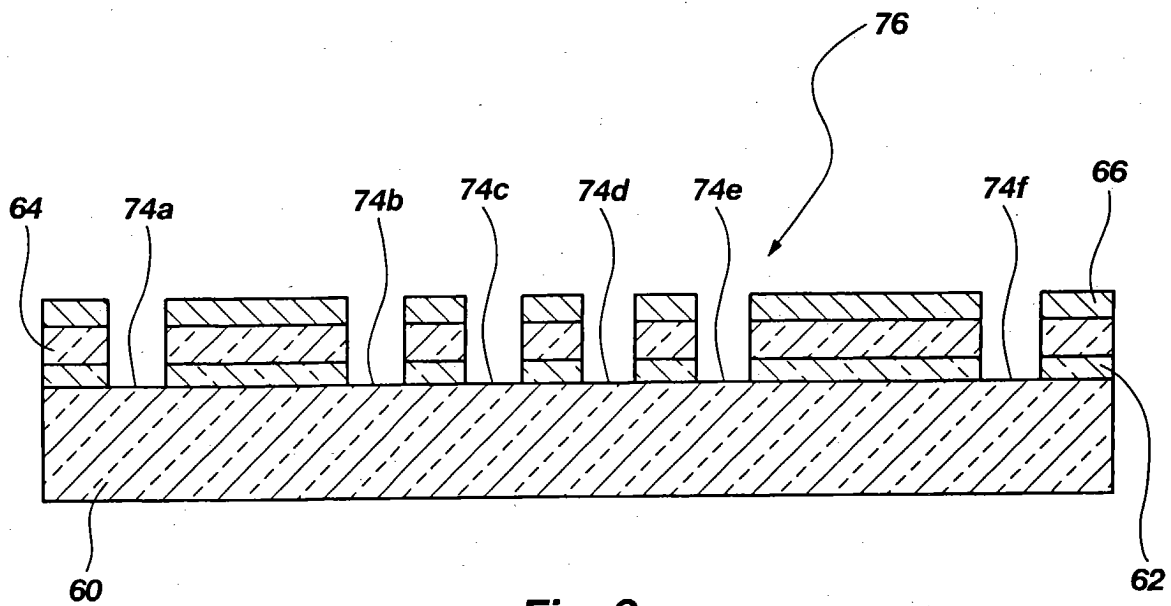
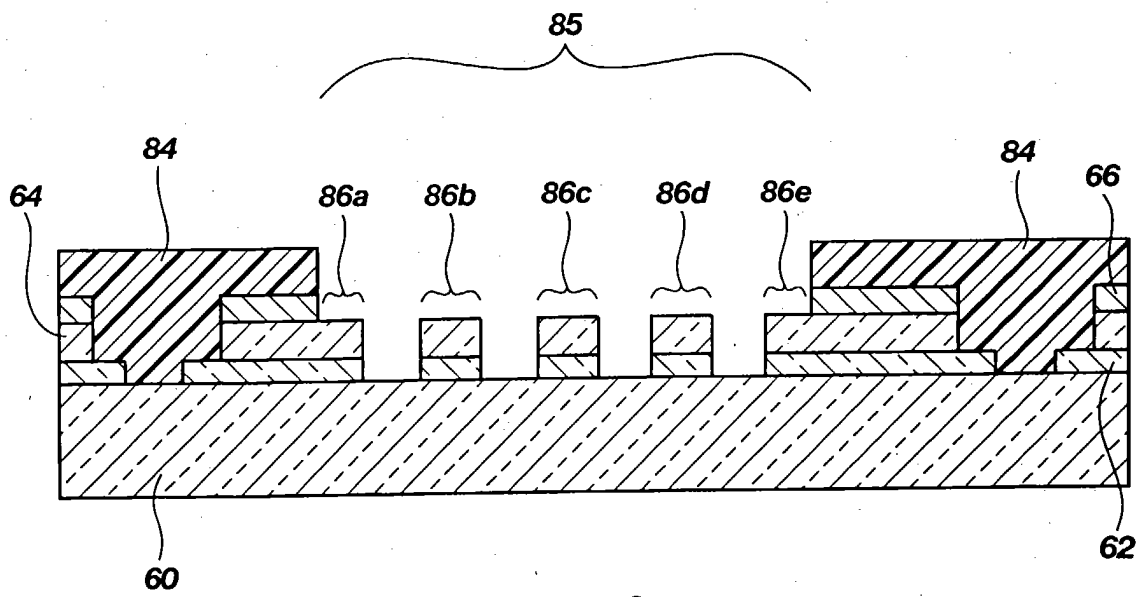
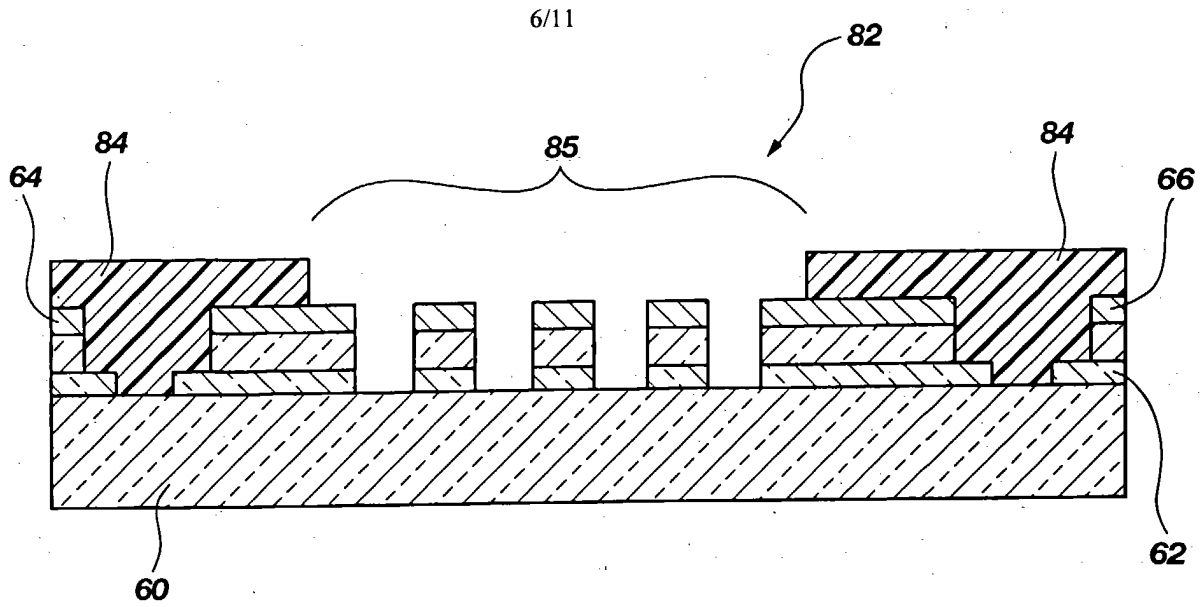


Fig. 6

A cross-sectional view of a semiconductor device. A substrate 60 is shown at the bottom, with a layer 62 on top of it. A series of patterned layers are formed on top of layer 62. These layers include a sequence of 74a, 74b, 74c, 74d, 74e, and 74f, which are separated by gaps. Between these layers, there are also layers 80a, 80b, 80c, and 80d. A layer 82 is shown on top of the 74f layer. The layers 74a-74f and 80a-80d are shown with different hatching patterns to indicate they are made of different materials.



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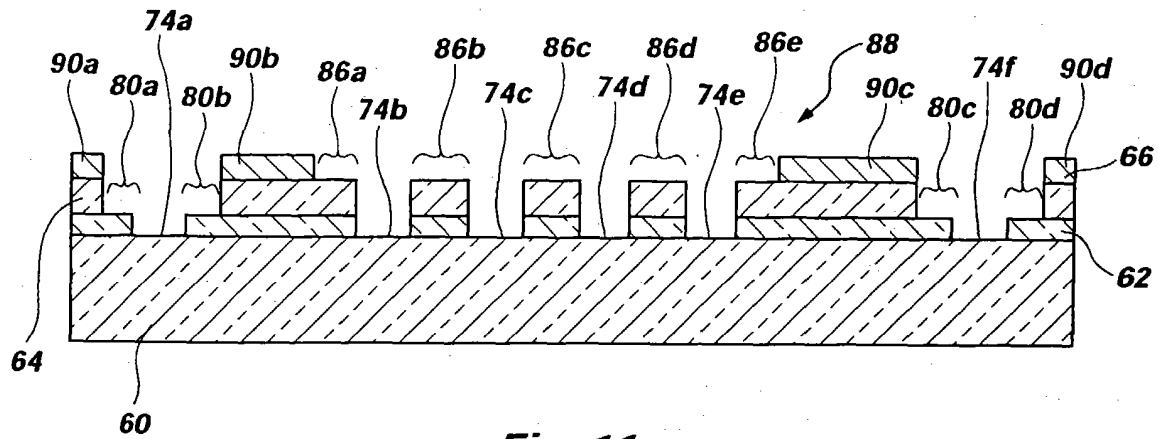


Fig. 11

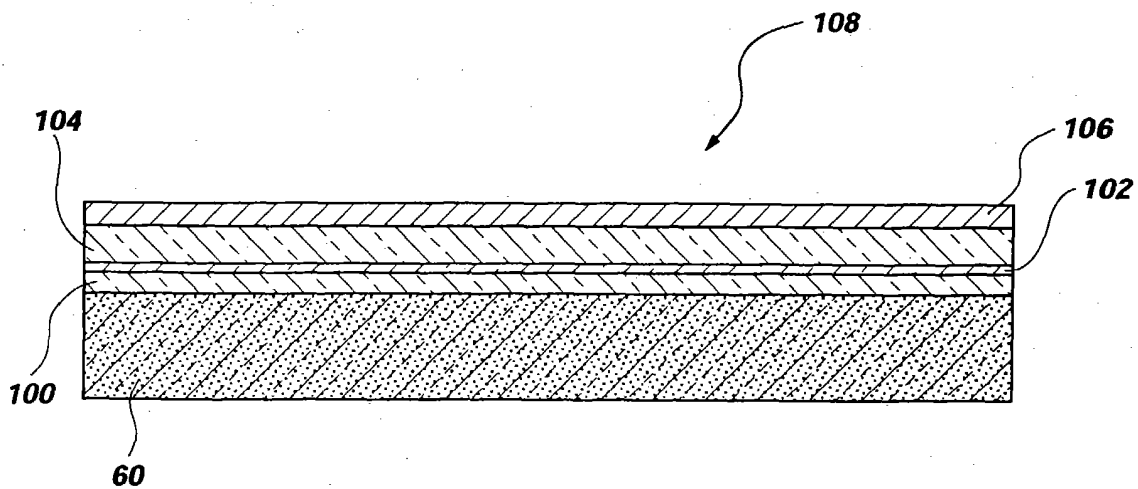


Fig. 12

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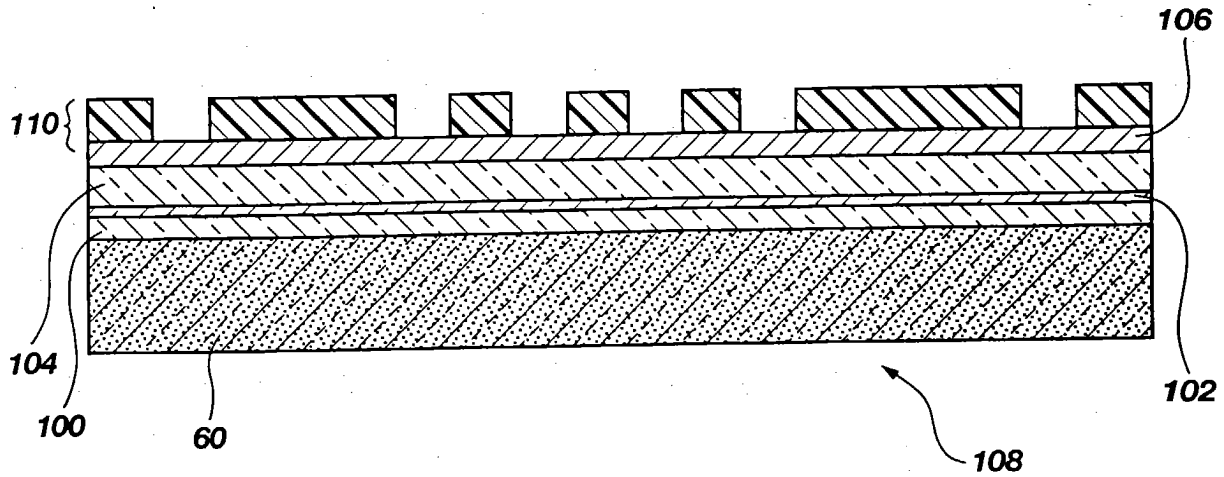


Fig. 13

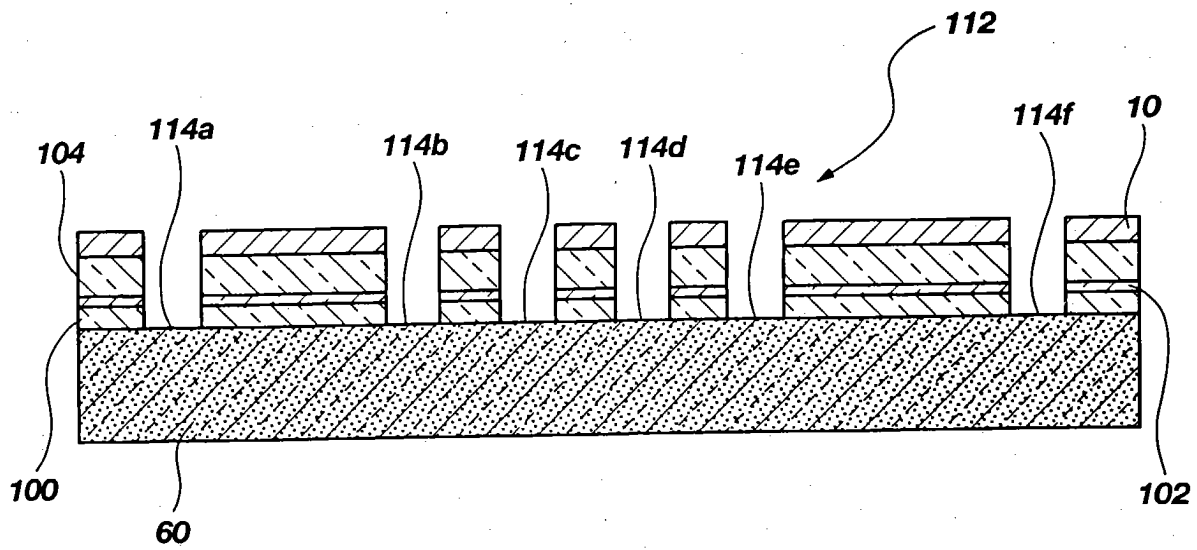


Fig. 14

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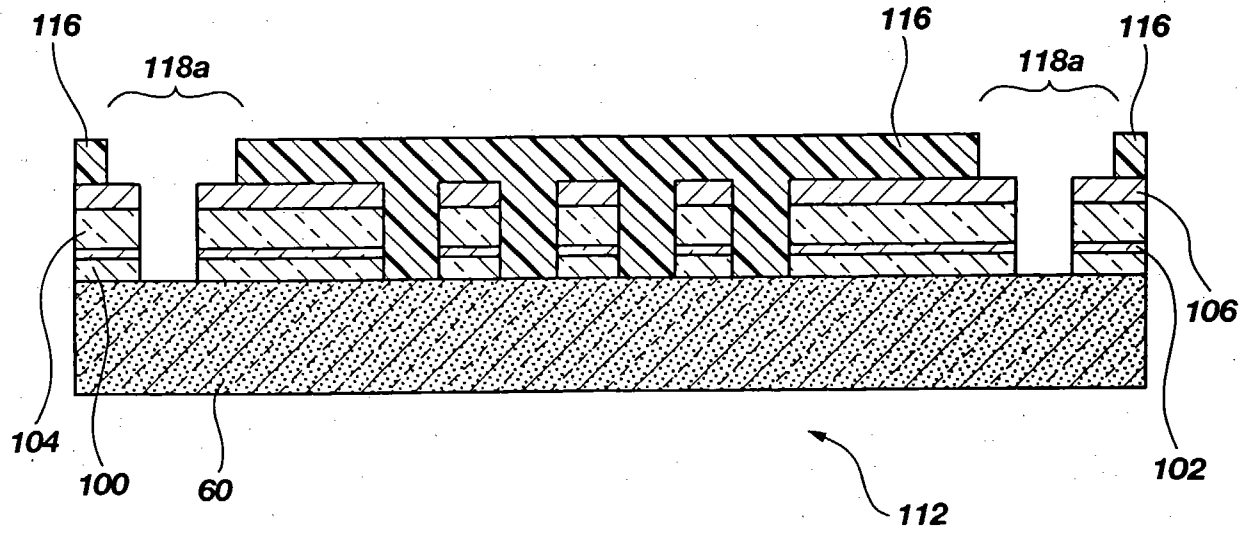


Fig. 15

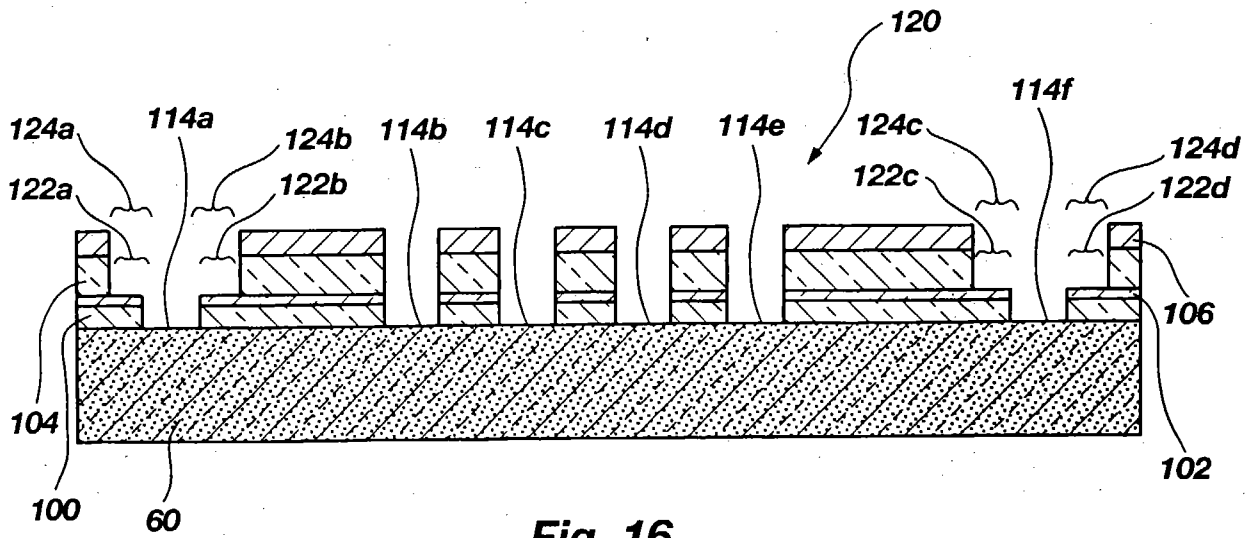


Fig. 16

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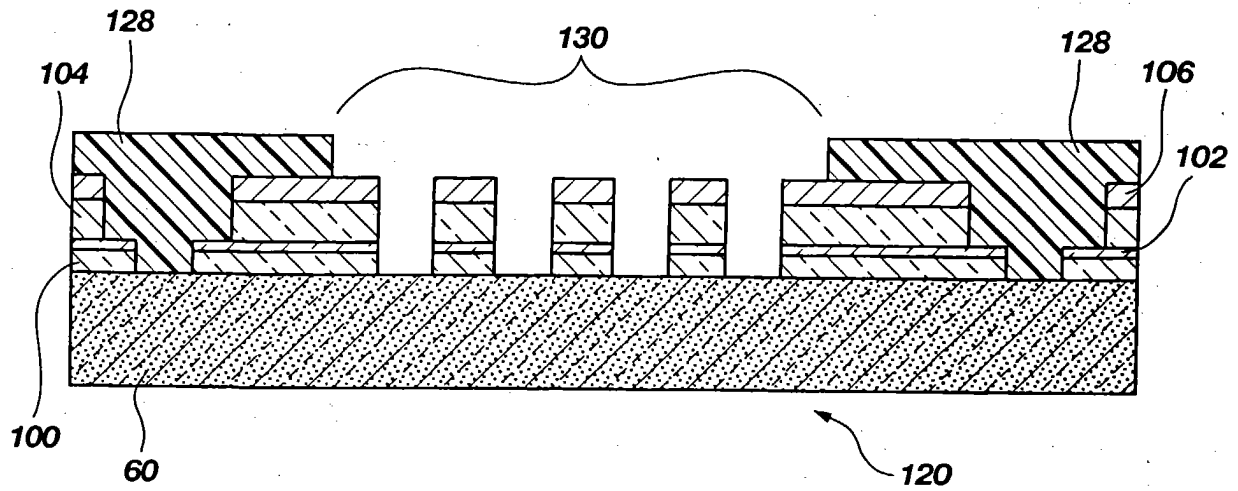


Fig. 17

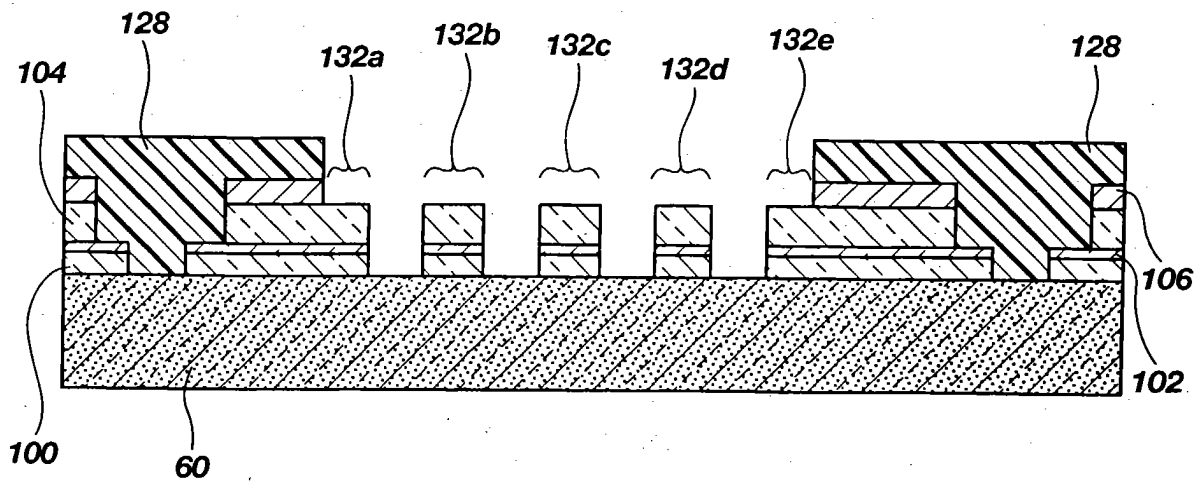


Fig. 18

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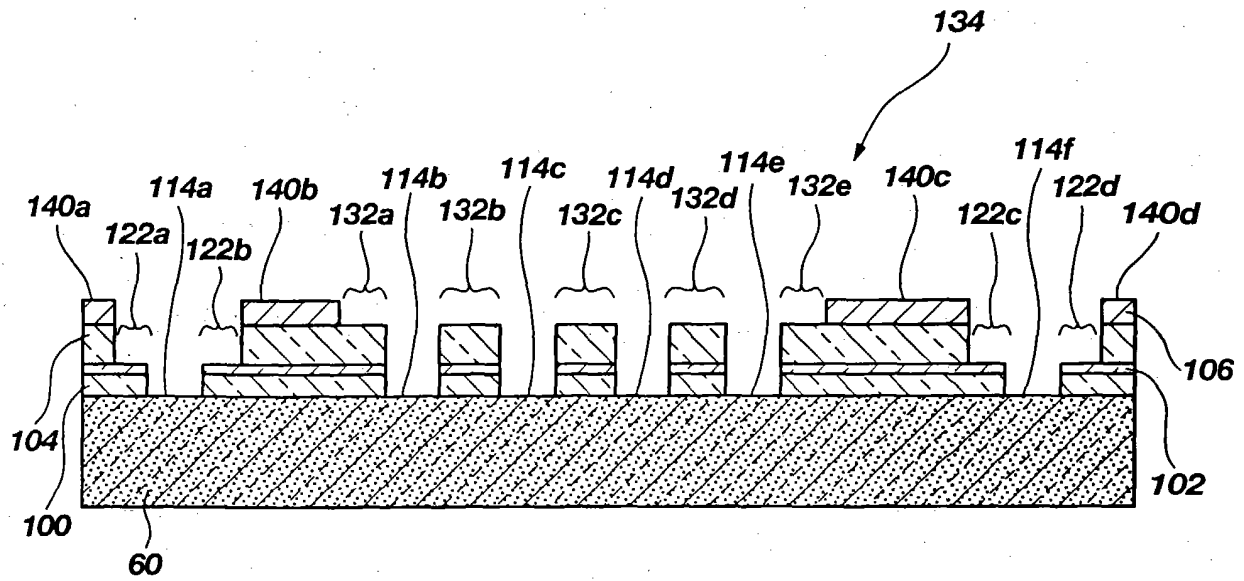


Fig. 19